

### Features

- Advanced Trench MOS Technology
- Low Gate Charge
- Low  $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available

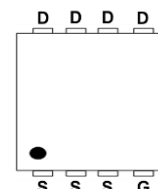
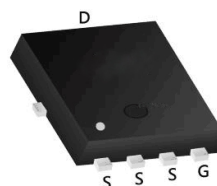
### Product Summary

BVDSS	RDSON	ID
60V	5.2mΩ	80A

### Application

- Motor Control.
- DC/DC Converter.
- Synchronous rectifier applications.

### DFN 5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current <sup>1,6</sup>	80	A
$I_D @ T_C = 100^\circ C$		51	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	300	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	92.5	mJ
$I_{AS}$	Avalanche Current	43	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>4</sup>	54.3	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup> ( $t \leq 10S$ )	---	25	$^\circ C/W$
	Thermal Resistance Junction-ambient <sup>1</sup> (Steady State)	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-case <sup>1</sup>	---	2.3	$^\circ C/W$

### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	60	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	4.4	5.2	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A	---	6.4	7.8	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.65	2.3	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	1.3	---	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =30V , V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	33.4	---	nC
Q <sub>g</sub>	Total Gate Charge (4.5V)		---	17.8	---	
Q <sub>gs</sub>	Gate-Source Charge		---	5.8	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	7.9	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3Ω, I <sub>D</sub> =20A	---	7.5	---	ns
T <sub>r</sub>	Rise Time		---	6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	29	---	
T <sub>f</sub>	Fall Time		---	7.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , f=1MHz	---	1625	---	pF
C <sub>oss</sub>	Output Capacitance		---	438	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	25	---	

### Diode Characteristics

I <sub>S</sub>	Continuous Source Current <sup>1,5,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	60	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =20A , dI/dt=400A/μs ,	---	23	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	60	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
2. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=43A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>S</sub> , in real applications , should be limited by total power dissipation.
- 6.The maximum current rating is package limited.

## Typical Characteristics

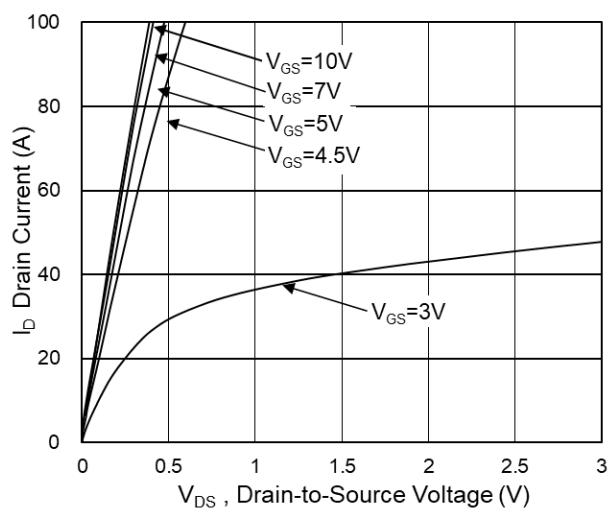


Fig.1 Typical Output Characteristics

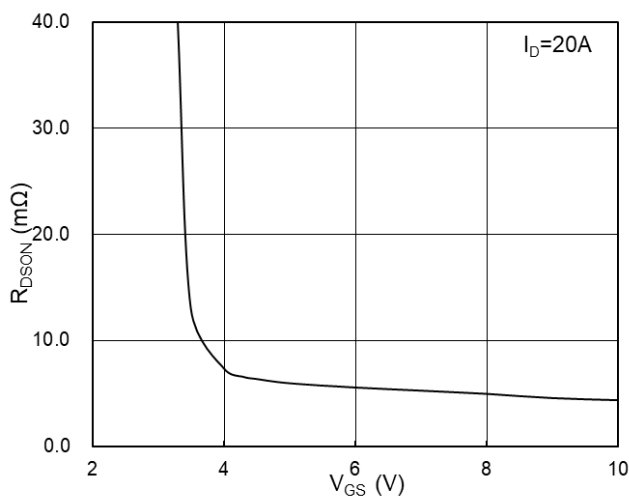


Fig.2 On-Resistance vs G-S Voltage

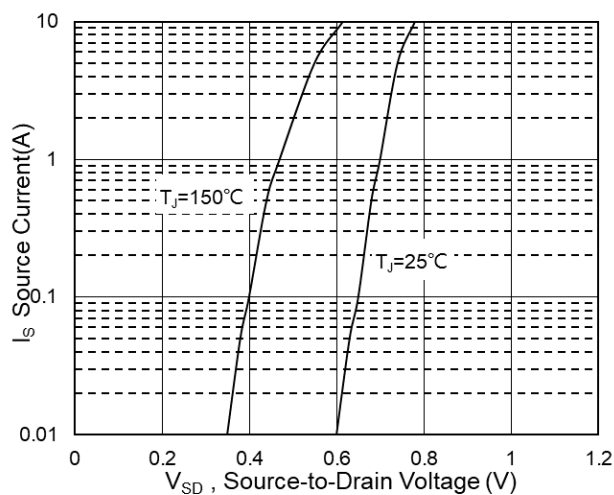


Fig.3 Source Drain Forward Characteristics

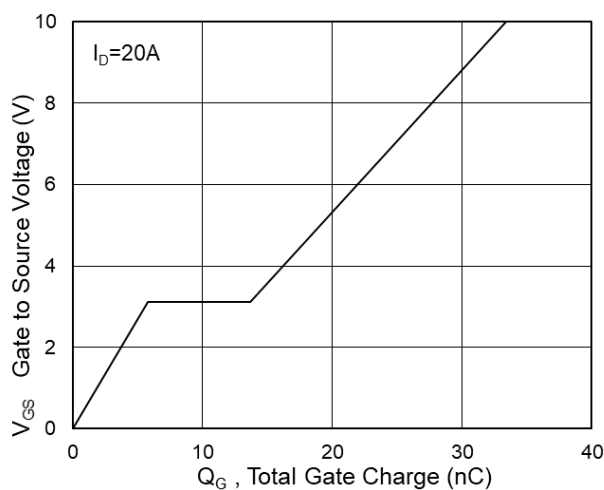


Fig.4 Gate-Charge Characteristics

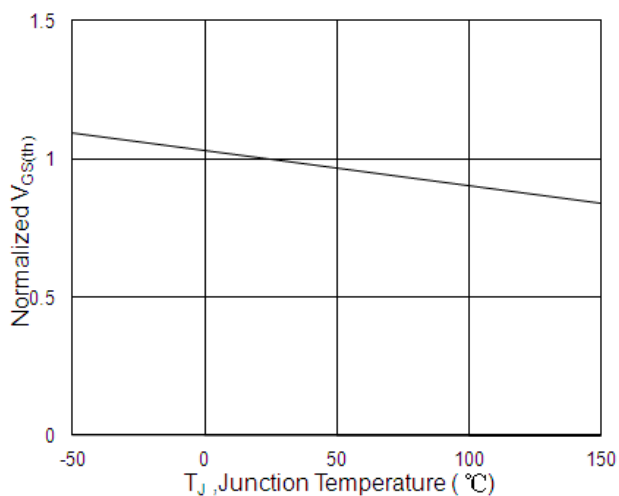


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

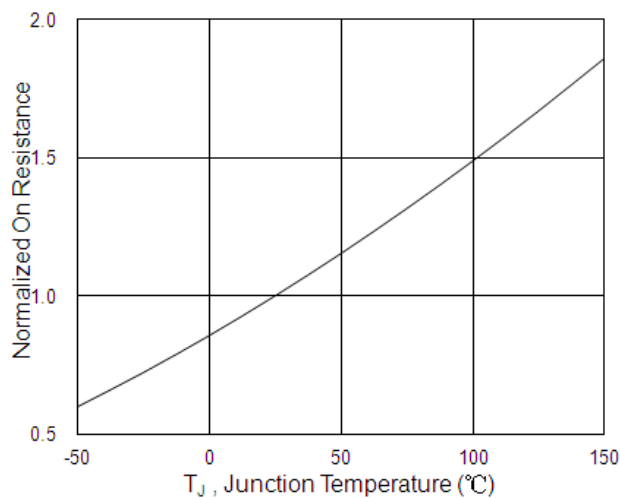


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$

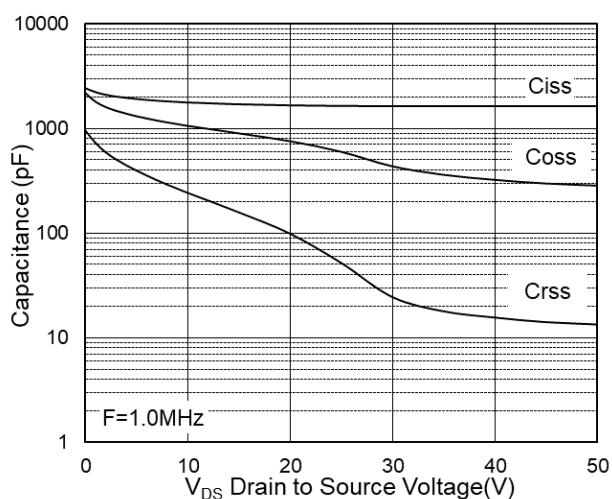


Fig.7 Capacitance

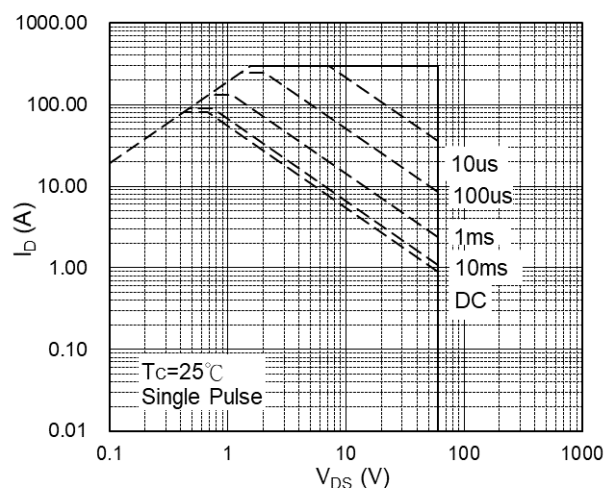


Fig.8 Safe Operating Area

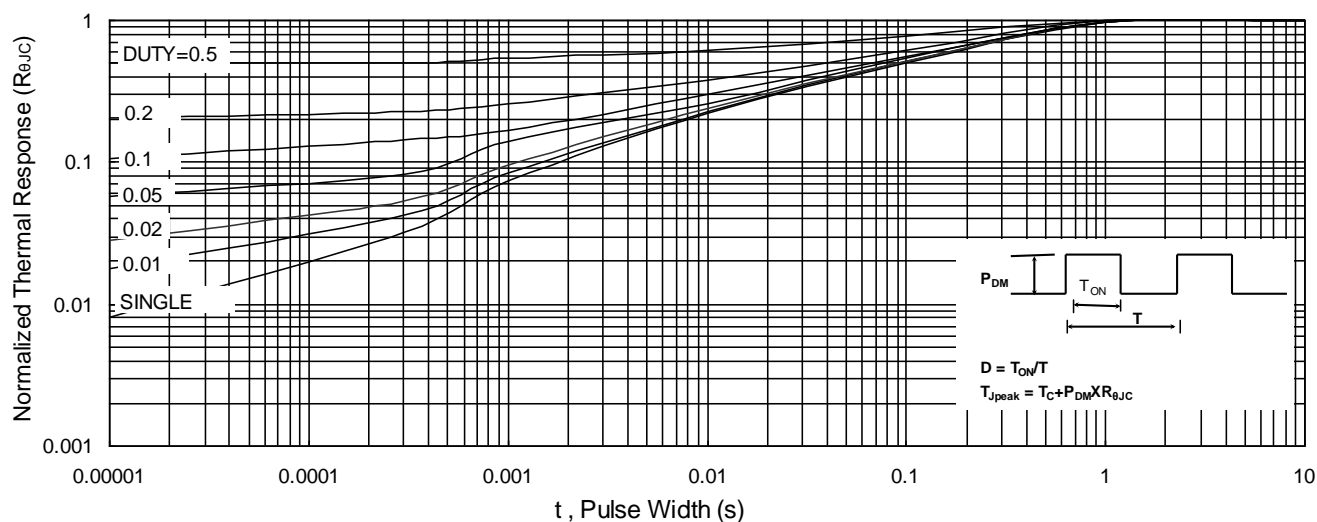


Fig.9 Normalized Maximum Transient Thermal Impedance

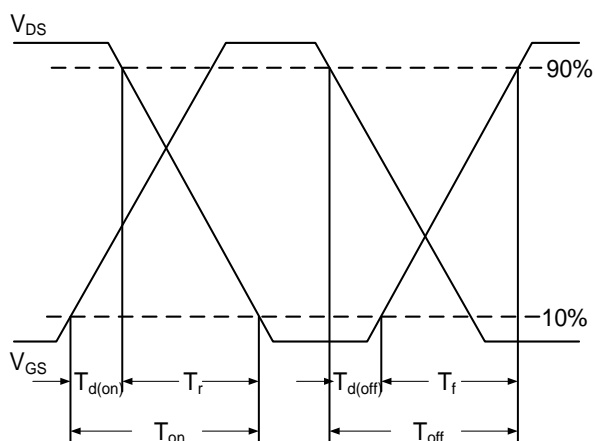


Fig.10 Switching Time Waveform

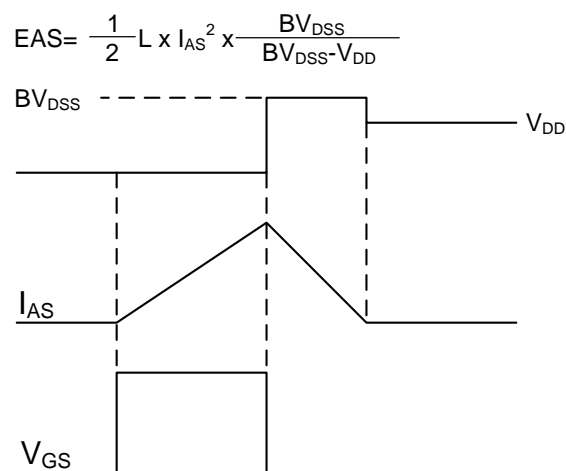
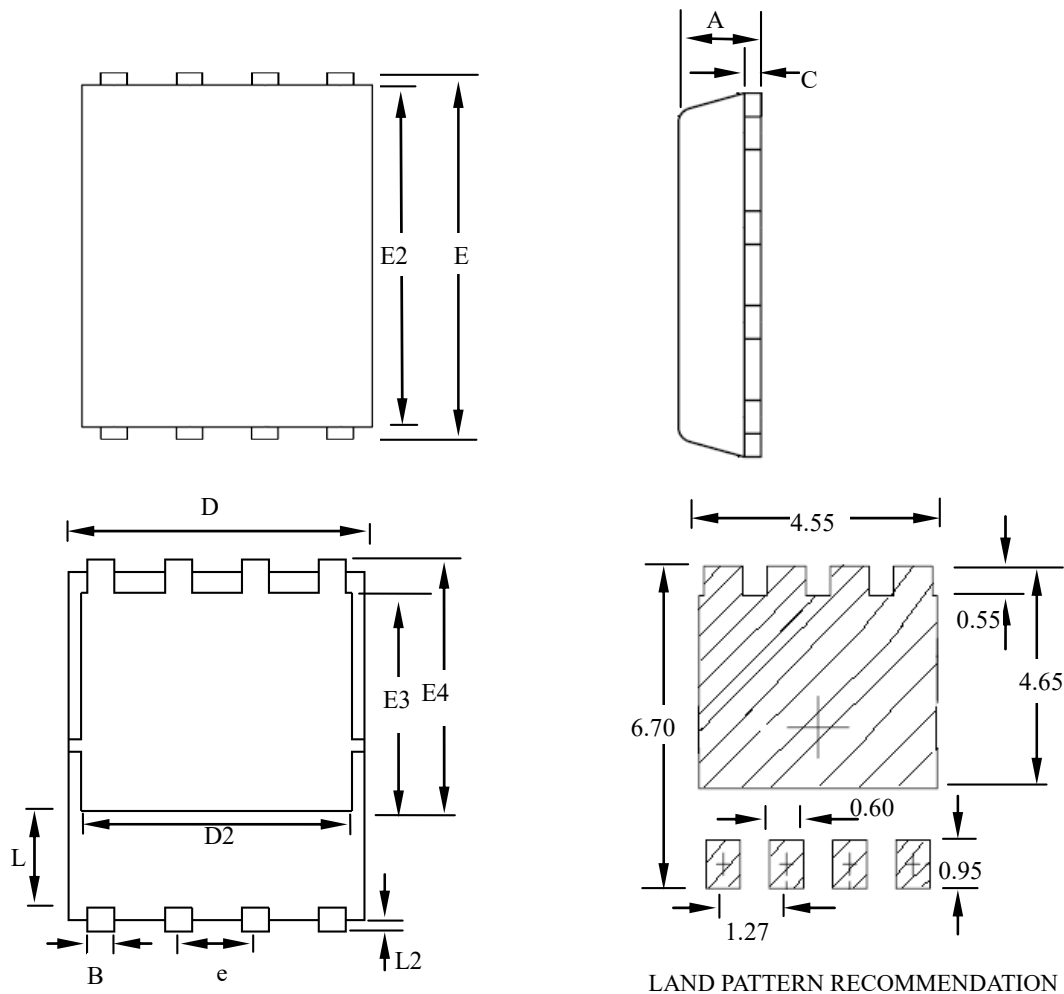


Fig.11 Unclamped Inductive Switching Waveform

## DFN5×6 Outline



LAND PATTERN RECOMMENDATION



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

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